

SURFACES OF ELECTRON  
DENSITY REDISTRIBUTION  
IN A ZnSe/GaAs HETEROSTRUCTURE  
WITH A MISFIT DISLOCATION WALL

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S u m m a r y

In the framework of the self-consistent electron-deformation model, the surface of the electron concentration distribution near a dislocation wall in a strained ZnSe/GaAs heterosystem has been calculated, and the change of its shape as a function of the average value of the conduction electron concentration and the distance between misfit dislocations has been studied. The profiles of the electron concentration surface have been demonstrated to be sinusoidal-like in the direction parallel to the misfit dislocation line and Gaussian-like in the direction perpendicular to it.